

# Supporting information

## Broadband and wide angle antireflection of sub-20 nm GaAs nanograss

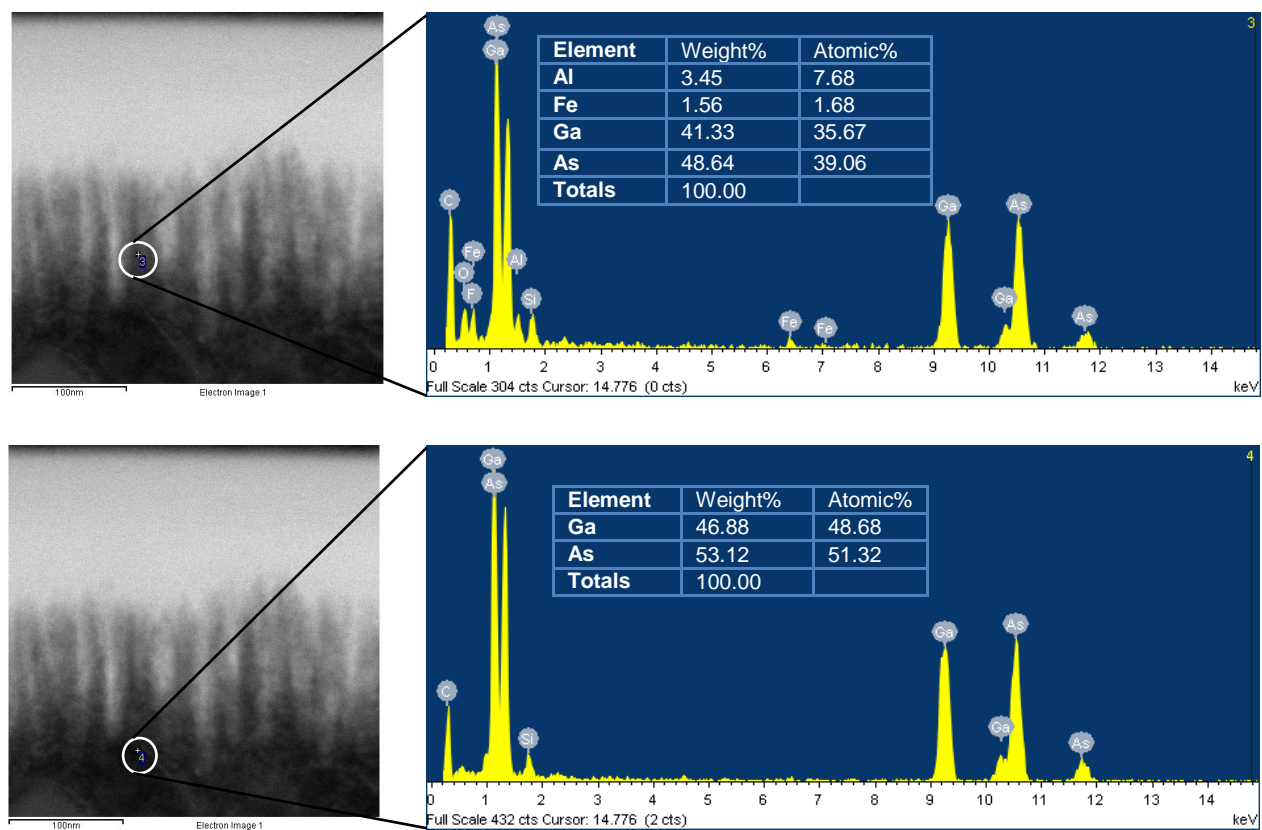
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**Figure S1.** EDS spectrum of the GaAs nanograss from top and bottom regions. Ga:As atomic compositions are 35:39 and 48:51 for top and bottom regions respectively. The presence of metal impurities gradually disappears on bottom regions.